MAXIMUM RATINGS

Symbol		Parameter	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to $+7.0$	V
VI	DC Input Voltage		$-0.5 \le V_1 \le +7.0$	V
Vo	DC Output Voltage	Output in Z or LOW State (Note 1)	$-0.5 \le V_O \le 7.0$	V
I _{IK}	DC Input Diode Current	V _I < GND	-50	mA
I _{OK}	DC Output Diode Current	V _O < GND	-50	mA
Io	DC Output Sink Current		±50	mA
I _{CC}	DC Supply Current per Supply	Pin	±100	mA
I _{GND}	DC Ground Current per Groun	d Pin	±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from	Case for 10 Seconds	260	°C
TJ	Junction Temperature under B	ias	+ 150	°C
θ_{JA}	Thermal Resistance	(Note 2)	333	°C/W
P _D	Power Dissipation in Still Air at	: 85°C	200	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	> 2000 > 200 N/A	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- I_O absolute maximum rating must be observed.
 Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- 3. Tested to EIA/JESD22-A114-A.
- 4. Tested to EIA/JESD22-A115-A.
- 5. Tested to JESD22-C101-A.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	Supply Voltage	Operating Data Retention Only	2.3 1.5	5.5 5.5	V
VI	Input Voltage	(Note 6)	0	5.5	V
Vo	Output Voltage	(HIGH or LOW State)	0	5.5	V
T _A	Operating Free-Air Temperature		-40	+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$ $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0 0	No Limit No Limit No Limit	ns/V

6. Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

DC ELECTRICAL CHARACTERISTICS

Symbol Parameter Condition (V) Min Typ Max Min Max Unit				V _{CC}	T _A = 25°C		$-40^{\circ}\text{C} \leq \text{T}_{\text{A}} \leq 85^{\circ}\text{C}$			
Voltage 2.7 1.2 1.7 2.0 1.2 2.0 3.0 1.3 1.9 2.2 1.3 2.2 4.5 1.9 2.7 3.1 1.9 3.1 5.5 2.2 3.3 3.6 2.2 3.6 3.6 3.7 3.1	Symbol	Parameter	Condition		Min	Тур	Max	Min	Max	Unit
V _T	V _T +			2.3	1.0	1.5	1.8	1.0	1.8	V
V _T		voitage		2.7	1.2	1.7	2.0	1.2	2.0	
V _T				3.0	1.3	1.9	2.2	1.3	2.2	
V _T				4.5	1.9	2.7	3.1	1.9	3.1	
Voltage Vol				5.5	2.2	3.3	3.6	2.2	3.6	
2.7 0.5 0.87 1.4 0.5 1.4 0.5 1.4 0.5 1.4 0.5 1.5 0.6 0.6 1.5 0.6 0.	V _T -			2.3	0.4	0.75	1.15	0.4	1.15	V
V _H Input Hysteresis Voltage V _{IN} = V _{IL} Output Voltage V _{IN} = V _{IH} or V _{IL} Input P _I V _{IL} Output Voltage V _{IN} = V _I Output Voltage		voltage		2.7	0.5	0.87	1.4	0.5	1.4	
No				3.0	0.6	1.0	1.5	0.6	1.5	
V _H Input Hysteresis Voltage				4.5	1.0	1.5	2.0	1.0	2.0	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$				5.5	1.2	1.9	2.3	1.2	2.3	
Note	V _H	Input Hysteresis Voltage		2.3	0.25	0.75	1.1	0.25	1.1	V
Voh High-Level Output Voltage I _{OH} = -100 μA 1.65 to 5.5 V _{CC} = 0.1 V _{CC} V _{CC} V _{CC} = 0.1 V _{CC} V _{CC} V _{CC} V _{CC} = 0.1 V _{CC} V _{CC} V _{CC} V _{CC} = 0.1 V _{CC} V _{CC}				2.7	0.3	0.83	1.15	0.3	1.15	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$				3.0	0.4	0.93	1.2	0.4	1.2	
$\begin{array}{c} V_{OH} \\ V_{IN} = V_{IH} \text{ or } V_{IL} \\ V_{IN} = V_{IH} \text{ or } V_{IL} \\ \end{array} \begin{array}{c} I_{OH} = -100 \ \mu A \\ I_{OH} = -3 \ mA \\ I_{OH} = -8 \ mA \\ I_{OH} = -12 \ mA \\ I_{OH} = -12 \ mA \\ I_{OH} = -24 \ mA \\ I_{OH} = -32 \ mA \\ \end{array} \begin{array}{c} 2.3 \\ 2.2 \\ 2.4 \\ 2.7 \\ 2.4 \\ 2.3 \\ 2.5 \\ 2.3 \\ 3.8 \\ \end{array} \begin{array}{c} 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.4 \\ 2.2 \\ 2.3 \\ 3.8 \\ 4.0 \\ \end{array} \\ \begin{array}{c} V_{OL} \\ V_{OL} \\ V_{IN} = V_{IH} \text{ or } V_{IL} \\ \end{array} \begin{array}{c} I_{OL} = 100 \ \mu A \\ I_{OL} = 100 \ \mu A \\ I_{OL} = 4 \ mA \\ I_{OL} = 8 \ mA \\ 2.3 \\ I_{OL} = 12 \ mA \\ I_{OL} = 12 \ mA \\ I_{OL} = 10 \ mA \\ I_{OL}$				4.5	0.6	1.2	1.5	0.6	1.5	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$				5.5	0.7	1.4	1.7	0.7	1.7	
I _{OH} = -3 mA	V _{OH}	High-Level Output Voltage	I _{OH} = -100 μA	1.65 to 5.5	V _{CC} -0.1	V_{CC}		V _{CC} −0.1		V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -3 \text{ mA}$	1.65	1.29	1.52		1.29		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_{OH} = -8 \text{ mA}$	2.3	1.9	2.1		1.9		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_{OH} = -12 \text{ mA}$	2.7	2.2	2.4		2.2		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_{OH} = -16 \text{ mA}$	3.0	2.4	2.7		2.4		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_{OH} = -24 \text{ mA}$	3.0	2.3	2.5		2.3		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_{OH} = -32 \text{ mA}$	4.5	3.8	4.0		3.8		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V _{OL}	Low-Level Output Voltage	I _{OL} = 100 μA	1.65 to 5.5			0.1		0.1	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 4 \text{ mA}$	1.65		0.08	0.24		0.24	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_{OL} = 8 \text{ mA}$	2.3		0.2	0.3		0.3	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			I _{OL} = 12 mA	2.7		0.22	0.4		0.4	
$I_{OL} = 32 \text{ mA}$ 4.5 0.42 0.55 0.55 I_{IN} Input Leakage Current $V_{IN} = V_{CC}$ or GND 0 to 5.5 ± 0.1 ± 1.0 μ I_{OFF} Power Off–Output Leakage $V_{OUT} = 5.5 V$ 0 1 1 10 μ			I _{OL} = 16 mA	3.0		0.28	0.4		0.4	
I_{IN} Input Leakage Current $V_{IN} = V_{CC}$ or GND 0 to 5.5 ± 0.1 ± 1.0 μ I_{OFF} Power Off–Output Leakage $V_{OUT} = 5.5$ V 0 1 1 10 μ			I _{OL} = 24 mA	3.0		0.38	0.55		0.55	
I_{OFF} Power Off–Output Leakage $V_{OUT} = 5.5 \text{ V}$ 0 1 10 μ			I _{OL} = 32 mA	4.5		0.42	0.55		0.55	
	I _{IN}	Input Leakage Current	$V_{IN} = V_{CC}$ or GND	0 to 5.5			±0.1		±1.0	μΑ
	l _{OFF}	Power Off-Output Leakage Current	V _{OUT} = 5.5 V	0			1		10	μΑ
I_{CC} Quiescent Supply Current $V_{IN} = V_{CC}$ or GND 5.5 1 1 10 μ	I _{CC}	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1		10	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_{\text{f}} = t_{\text{f}} = 3.0 \text{ ns}$)

			V _{CC}		T _A = 25°C		$-40^{\circ}\text{C} \leq \text{T}_{\text{A}} \leq 85^{\circ}\text{C}$		
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
t _{PLH}	Propagation Delay	$R_L = 1 \text{ M}\Omega$, $C_L = 15 \text{ pF}$	2.5 ± 0.2	1.8	4.3	7.4	1.8	8.1	ns
t _{PHL} Input A to Y (Figures 3 and 4)		$R_L = 1 \text{ M}\Omega$, $C_L = 15 \text{ pF}$	3.3 ± 0.3	1.5	3.3	5.0	1.5	5.5	
		$R_L = 500 \Omega, C_L = 50 pF$		1.8	4.0	5.0	1.8	6.6	
	Î	$R_L = 1 \text{ M}\Omega$, $C_L = 15 \text{ pF}$	5.0 ± 0.5	1.0	2.7	4.1	1.0	4.5	
		$R_L = 500 \Omega, C_L = 50 pF$		1.2	3.2	4.9	1.2	5.4	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	2.5	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	9	pF
	(Note 7)	10 MHz, V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	11	

^{7.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

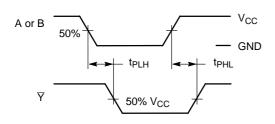
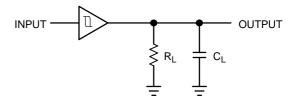


Figure 3. Switching Waveforms



A 1–MHz square input wave is recommended for propagation delay tests.

Figure 4. Test Circuit

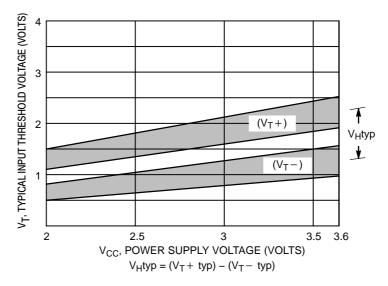
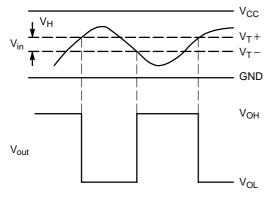
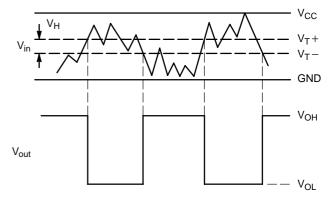


Figure 5. Typical Input Threshold, $V_T +$, $V_T -$ versus Power Supply Voltage





(a) A Schmitt–Trigger Squares Up Inputs With Slow Rise and Fall Times

(b) A Schmitt-Trigger Offers Maximum Noise Immunity

Figure 6. Typical Schmitt-Trigger Applications

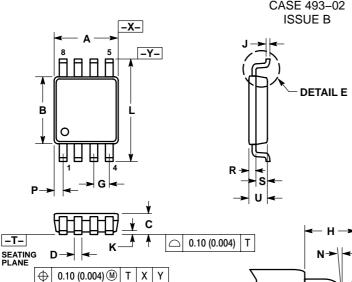
DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Tape and Reel Size [†]
NL37WZ17US	US8	178 mm, 3000 Units / Tape & Reel
NL37WZ17USG	US8 (Pb-Free)	178 mm, 3000 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

US8 US SUFFIX CASE 493-02 ISSUE B



NOTES:

R 0.10 TYP

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION "A" DOES NOT INCLUDE MOLD
- DIMENSION "A" DOES NOT INCLUDE MOL FLASH, PROTRUSION OR GATE BURR. MOLD FLASH. PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.140 MM (0.0055") PER SIDE.
- (0.0055") PER SIDE.

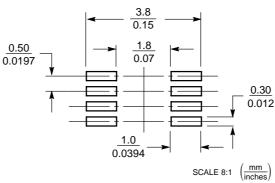
 4. DIMENSION "B" DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSION. INTER-LEAD FLASH AND PROTRUSION SHALL NOT E3XCEED 0.140 (0.0055") PER SIDE.
- 5. LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076–0.0203 MM. (300–800 °). 6. ALL TOLERANCE UNLESS OTHERWISE
- ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 (0.0002 ").

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.90	2.10	0.075	0.083	
В	2.20	2.40	0.087	0.094	
С	0.60	0.90	0.024	0.035	
D	0.17	0.25	0.007	0.010	
F	0.20	0.35	0.008	0.014	
G	0.50	BSC	0.020 BSC		
Н	0.40	REF	0.016	REF	
J	0.10	0.18	0.004	0.007	
K	0.00	0.10	0.000	0.004	
L	3.00	3.20	0.118	0.126	
M	0 °	6 °	0 °	6 °	
N	5 °	10 °	5 °	10 °	
Р	0.23	0.34	0.010	0.013	
R	0.23	0.33	0.009	0.013	
S	0.37	0.47	0.015	0.019	
U	0.60	0.80	0.024	0.031	
V	0.12	BSC	0.005 BSC		

SOLDERING FOOTPRINT*

DETAIL E

F



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use a components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.